MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRIODE THYRISTOR (BI-DIRECTIONAL), SILICON,

TYPES 2N5806 THROUGH 2N5809

This amendment forms a part of Military Specification MIL-S-19500/438, dated 20 August 1970, and is approved for use by all Departments and Agencies of the Department of Defense.

PAGE 11

Table III, group C inspection, subgroup 7, delete and substitute:

Examination or test	MIL-STD-750		LTPD	Symbol	Limits		Unit
	Method	Details			Min	Max	
Subgroup 7			λ=20				
Off-state voltage life test	---	(See figure 3) T_C = 115°C		---			
2N5806		V_{DRM} = 200 v(pk)			---	---	---
2N5807		V_{DRM} = 400 v(pk)			---	---	---
2N5808		V_{DRM} = 500 v(pk)			---	---	---
2N5809		V_{DRM} = 600 v(pk)			---	---	---
End points: (See 4.5.3.)							
Thermal fatigue		$I_{T(RMS)}$ = 25A, 60Hz ΔT = 40°C (1 Min. on, 3 Min. off ±.5 Min = 1 cycle) 4,000 cycles					
End points: (see 4.5.3) Same as subgroup 4 of group B.							

Custodians:
Army - EL
Navy - EC
Air Force - 17

Review activities:
Army - MU, MI
Navy -
Air Force - 11, 19, 80, 85
DSA - ES
NASA - NA

User activities:
Army - SM
Navy - CG, MC, OS, AS, SH

Preparing activity:
Navy - EC

Agent:
DSA - ES

(Project 5961-0613)